

## General Description

The GreenMOS<sup>®</sup> high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS<sup>®</sup> Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS<sup>®</sup>



## Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

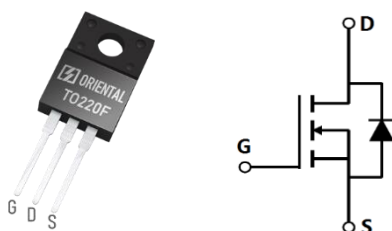
## Key Performance Parameters

| Parameter                         | Value | Unit      |
|-----------------------------------|-------|-----------|
| $V_{DS}$                          | 650   | V         |
| $I_D$ , pulse                     | 60    | A         |
| $R_{DS(ON)}$ , max @ $V_{GS}=10V$ | 200   | $m\Omega$ |
| $Q_g$                             | 24    | nC        |

## Marking Information

| Product Name  | Package | Marking      |
|---------------|---------|--------------|
| OSG65R200FT3F | TO220F  | OSG65R200FT3 |

## Package & Pin Information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

| Parameter                                                                 | Symbol                | Value      | Unit               |
|---------------------------------------------------------------------------|-----------------------|------------|--------------------|
| Drain-source voltage                                                      | $V_{DS}$              | 650        | V                  |
| Gate-source voltage                                                       | $V_{GS}$              | $\pm 30$   | V                  |
| Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$         | $I_D$                 | 20         | A                  |
| Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}\text{C}$        |                       | 12.6       |                    |
| Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{D, \text{pulse}}$ | 60         | A                  |
| Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$ | $I_S$                 | 20         | A                  |
| Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{S, \text{pulse}}$ | 60         | A                  |
| Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$                | $P_D$                 | 34         | W                  |
| Single pulsed avalanche energy <sup>4)</sup>                              | $E_{AS}$              | 254        | mJ                 |
| MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 480\text{ V}$                    | dv/dt                 | 50         | V/ns               |
| Reverse diode dv/dt, $V_{DS}=0\ldots 480\text{ V}$ , $I_{SD}\leq I_D$     | dv/dt                 | 15         | V/ns               |
| Operation and storage temperature                                         | $T_{stg}, T_j$        | -55 to 150 | $^{\circ}\text{C}$ |

**Thermal Characteristics**

| Parameter                            | Symbol          | Value | Unit                 |
|--------------------------------------|-----------------|-------|----------------------|
| Thermal resistance, junction-case    | $R_{\theta JC}$ | 3.68  | $^{\circ}\text{C/W}$ |
| Thermal resistance, junction-ambient | $R_{\theta JA}$ | 62.5  | $^{\circ}\text{C/W}$ |

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

| Parameter                        | Symbol       | Min. | Typ. | Max. | Unit          | Test condition                                                       |
|----------------------------------|--------------|------|------|------|---------------|----------------------------------------------------------------------|
| Drain-source breakdown voltage   | $BV_{DSS}$   | 650  |      |      | V             | $V_{GS}=0\text{ V}$ , $I_D=250\text{ }\mu\text{A}$                   |
| Gate threshold voltage           | $V_{GS(th)}$ | 3.5  |      | 4.5  | V             | $V_{DS}=V_{GS}$ , $I_D=250\text{ }\mu\text{A}$                       |
| Drain-source on-state resistance | $R_{DS(ON)}$ |      | 0.16 | 0.20 | $\Omega$      | $V_{GS}=10\text{ V}$ , $I_D=10\text{ A}$                             |
|                                  |              |      | 0.42 |      |               | $V_{GS}=10\text{ V}$ , $I_D=10\text{ A}$ , $T_j=150^{\circ}\text{C}$ |
| Gate-source leakage current      | $I_{GSS}$    |      |      | 100  | nA            | $V_{GS}=30\text{ V}$                                                 |
|                                  |              |      |      | -100 |               | $V_{GS}=-30\text{ V}$                                                |
| Drain-source leakage current     | $I_{DSS}$    |      |      | 1    | $\mu\text{A}$ | $V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$                          |
| Gate resistance                  | $R_G$        |      | 22   |      | $\Omega$      | $f = 1\text{ MHz}$ , Open drain                                      |

### Dynamic Characteristics

| Parameter                                    | Symbol       | Min. | Typ. | Max. | Unit | Test condition                                                                              |
|----------------------------------------------|--------------|------|------|------|------|---------------------------------------------------------------------------------------------|
| Input capacitance                            | $C_{iss}$    |      | 842  |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=50\text{ V}$ ,<br>$f=100\text{ kHz}$                       |
| Output capacitance                           | $C_{oss}$    |      | 58   |      | pF   |                                                                                             |
| Reverse transfer capacitance                 | $C_{rss}$    |      | 2.5  |      | pF   |                                                                                             |
| Effective output capacitance, energy related | $C_{o(er)}$  |      | 40   |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=0\text{ V-400 V}$                                          |
| Effective output capacitance, time related   | $C_{o(tr)}$  |      | 226  |      | pF   |                                                                                             |
| Turn-on delay time                           | $t_{d(on)}$  |      | 30.2 |      | ns   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=400\text{ V}$ ,<br>$R_G=2\ \Omega$ ,<br>$I_D=20\text{ A}$ |
| Rise time                                    | $t_r$        |      | 72.8 |      | ns   |                                                                                             |
| Turn-off delay time                          | $t_{d(off)}$ |      | 65.2 |      | ns   |                                                                                             |
| Fall time                                    | $t_f$        |      | 34   |      | ns   |                                                                                             |

### Gate Charge Characteristics

| Parameter            | Symbol        | Min. | Typ. | Max. | Unit | Test condition                                                         |
|----------------------|---------------|------|------|------|------|------------------------------------------------------------------------|
| Total gate charge    | $Q_g$         |      | 24   |      | nC   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=400\text{ V}$ ,<br>$I_D=20\text{ A}$ |
| Gate-source charge   | $Q_{gs}$      |      | 6    |      | nC   |                                                                        |
| Gate-drain charge    | $Q_{gd}$      |      | 12   |      | nC   |                                                                        |
| Gate plateau voltage | $V_{plateau}$ |      | 7    |      | V    |                                                                        |

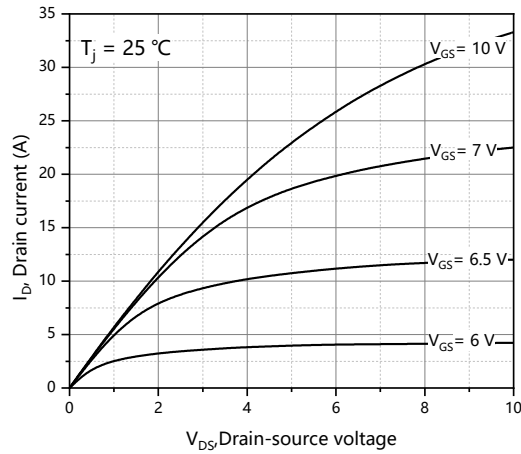
### Body Diode Characteristics

| Parameter                     | Symbol    | Min. | Typ. | Max. | Unit          | Test condition                                                                  |
|-------------------------------|-----------|------|------|------|---------------|---------------------------------------------------------------------------------|
| Diode forward voltage         | $V_{SD}$  |      |      | 1.3  | V             | $I_S=20\text{ A}$ ,<br>$V_{GS}=0\text{ V}$                                      |
| Reverse recovery time         | $t_{rr}$  |      | 350  |      | ns            | $V_R=400\text{ V}$ ,<br>$I_S=20\text{ A}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge       | $Q_{rr}$  |      | 4.8  |      | $\mu\text{C}$ |                                                                                 |
| Peak reverse recovery current | $I_{rrm}$ |      | 25.3 |      | A             |                                                                                 |

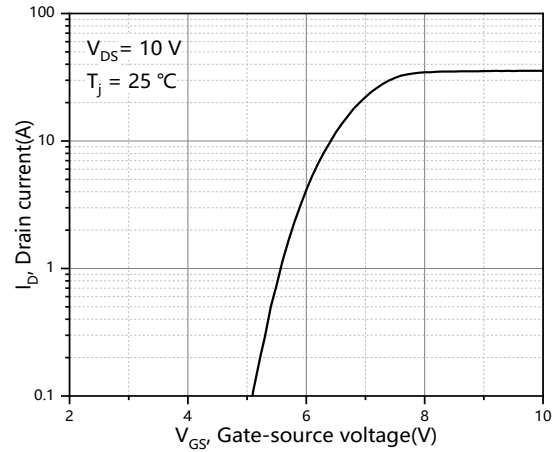
### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4)  $V_{DD}=100\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=75\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

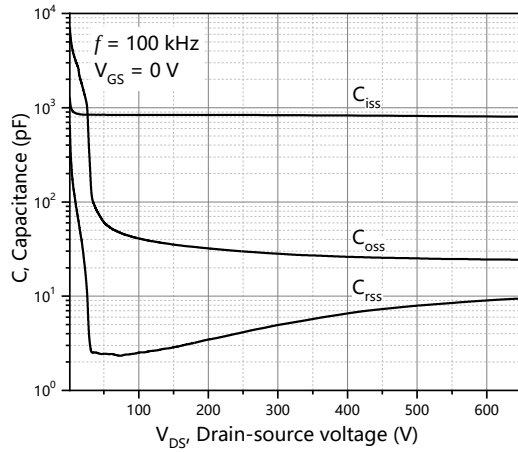
## Electrical Characteristics Diagrams



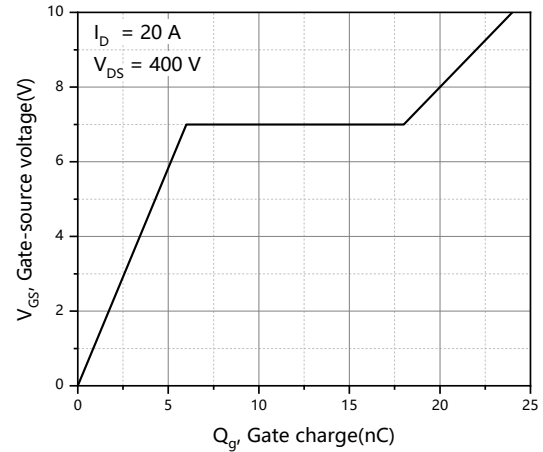
**Figure 1. Typ. output characteristics**



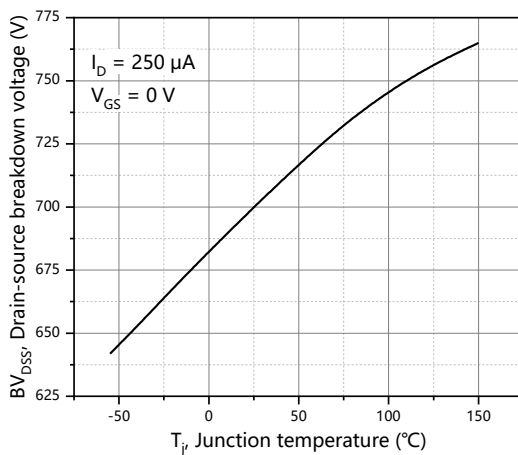
**Figure 2. Typ. transfer characteristics**



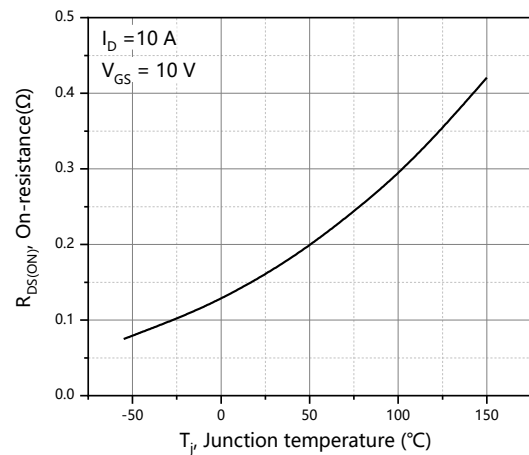
**Figure 3. Typ. capacitances**



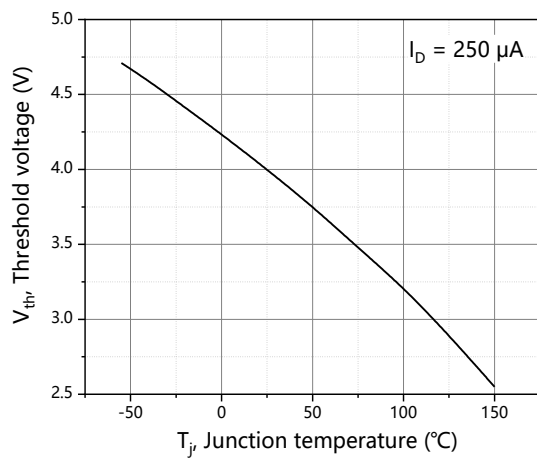
**Figure 4. Typ. gate charge**



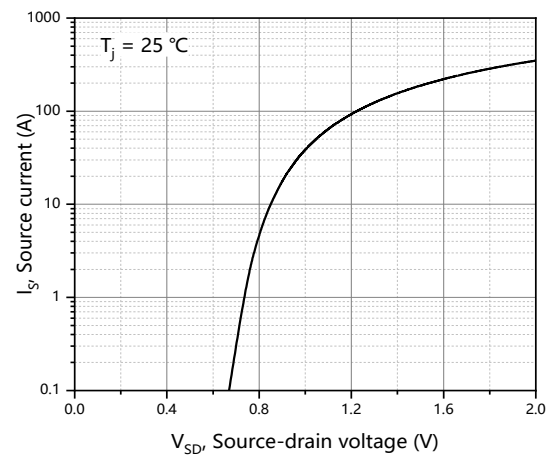
**Figure 5. Drain-source breakdown voltage**



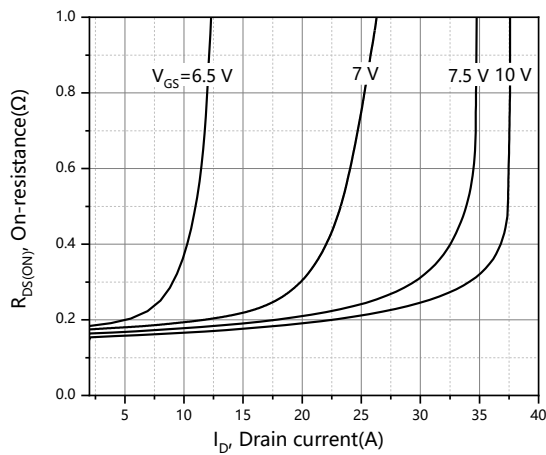
**Figure 6. Drain-source on-state resistance**



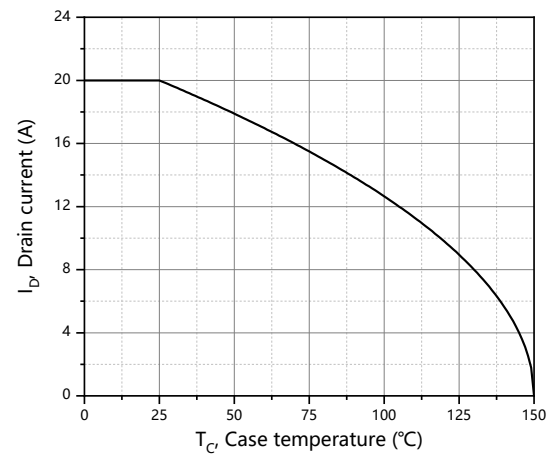
**Figure 7. Threshold voltage**



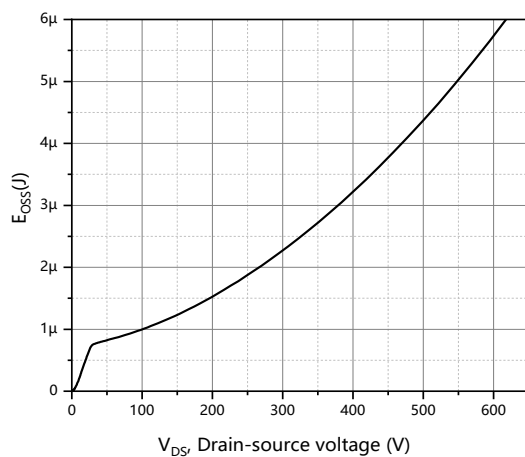
**Figure 8. Forward characteristic of body diode**



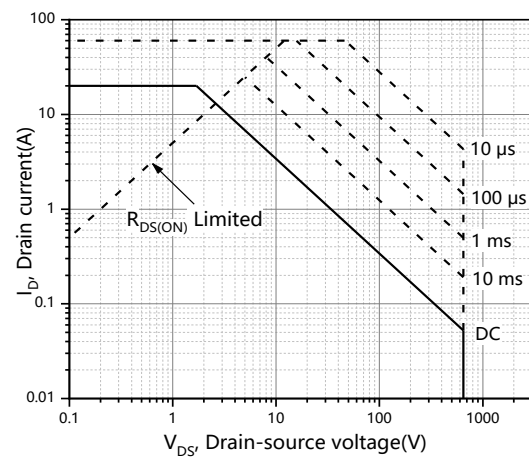
**Figure 9. Drain-source on-state resistance**



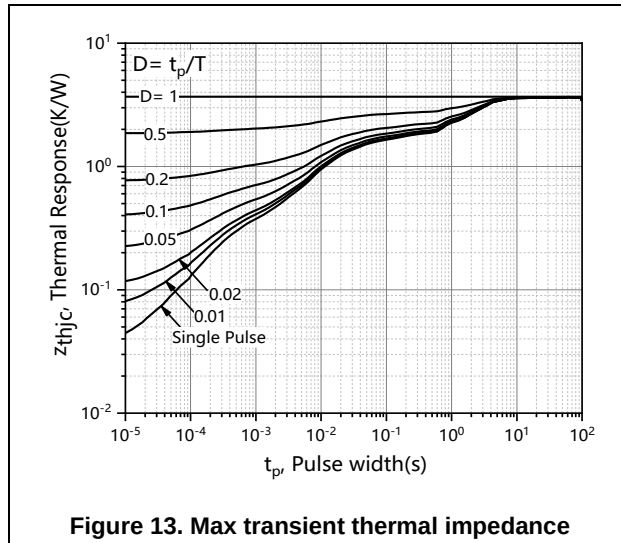
**Figure 10. Drain current**



**Figure 11. Typ. Coss stored energy**

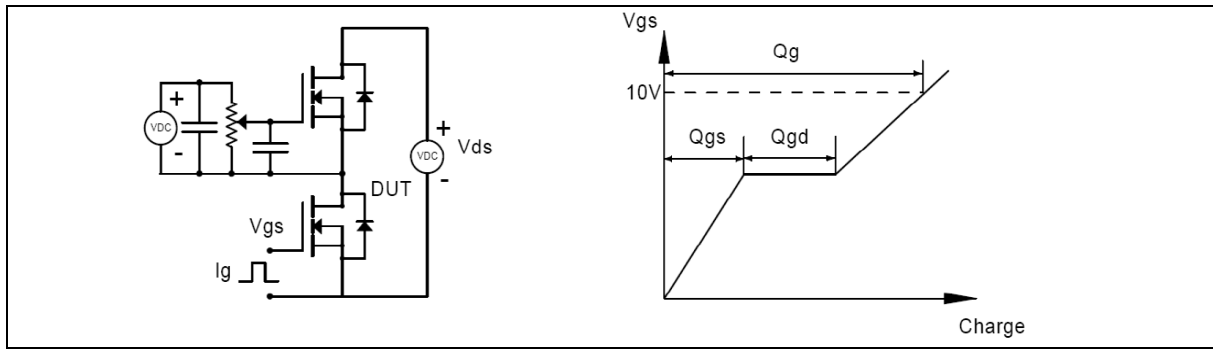


**Figure 12. Safe operation area for T<sub>C</sub>=25°C**

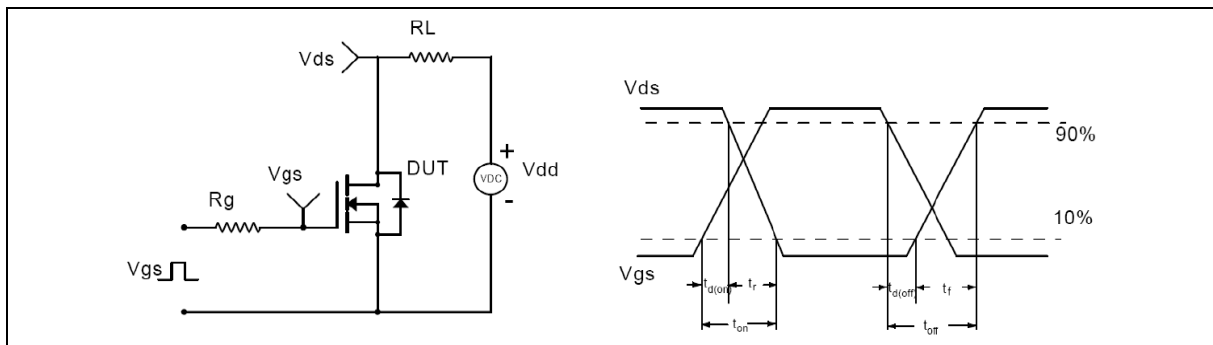


**Figure 13. Max transient thermal impedance**

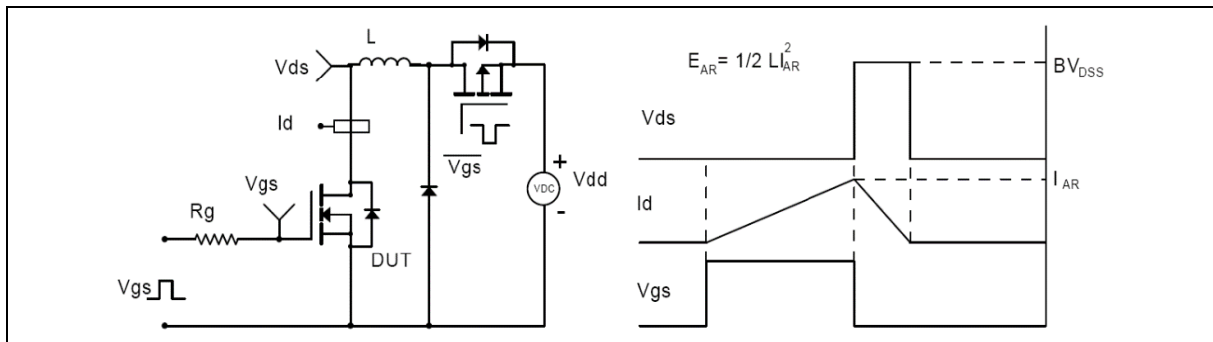
## Test circuits and waveforms



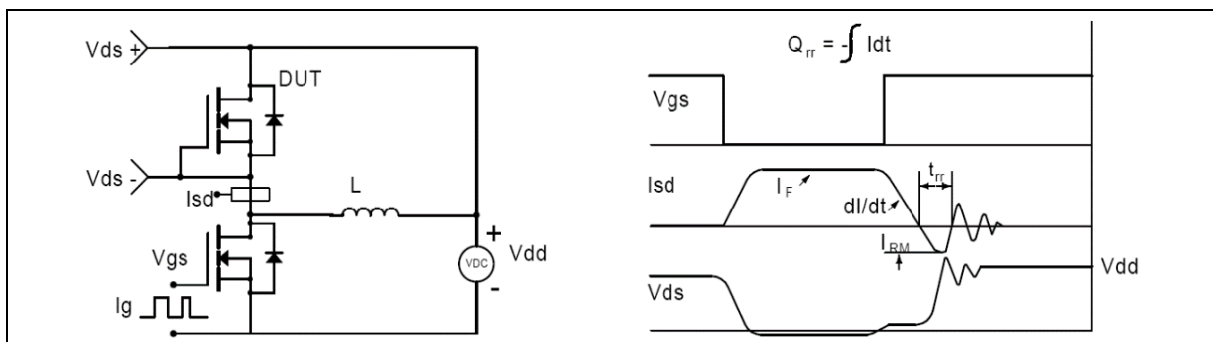
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

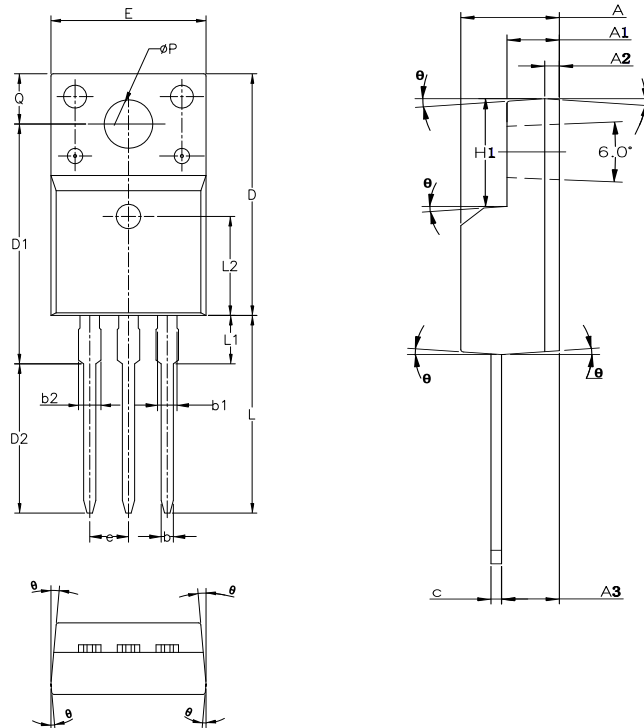


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information



| Symbol | mm       |       |       |
|--------|----------|-------|-------|
|        | Min      | Nom   | Max   |
| A      | 4.50     | 4.70  | 4.83  |
| A1     | 2.34     | 2.54  | 2.74  |
| A2     | 0.70 REF |       |       |
| A3     | 2.56     | 2.76  | 2.93  |
| b      | 0.70     | -     | 0.90  |
| b1     | 1.18     | -     | 1.38  |
| b2     | -        | -     | 1.47  |
| c      | 0.45     | 0.50  | 0.60  |
| D      | 15.67    | 15.87 | 16.07 |
| D1     | 15.55    | 15.75 | 15.95 |
| D2     | 9.60     | 9.80  | 10.00 |
| E      | 9.96     | 10.16 | 10.36 |
| e      | 2.54 BSC |       |       |
| H1     | 6.48     | 6.68  | 6.88  |
| L      | 12.68    | 12.98 | 13.28 |
| L1     | -        | -     | 3.50  |
| L2     | 6.50 REF |       |       |
| ΦP     | 3.08     | 3.18  | 3.28  |
| Q      | 3.20     | -     | 3.40  |
| θ      | 1°       | 3°    | 5°    |

Version 1: TO20F-J package outline dimension



### Ordering Information

| Package Type | Units/ Tube | Tubes/ Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|--------------|-------------|------------------|------------------|-------------------------|-------------------|
| TO220F-J     | 50          | 20               | 1000             | 5                       | 5000              |

### Product Information

| Product       | Package | Pb Free | RoHS | Halogen Free |
|---------------|---------|---------|------|--------------|
| OSG65R200FT3F | TO220F  | yes     | yes  | yes          |

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